

# **32Gb (2G x 16)** DDR4 SDRAM

**AS4C2G16D4 -** 128 Meg x 16 x 16 Banks x 1 Ranks

**Revision History** 

Revision	Details	Date
Rev 1.0	Initial Release	Sept. 2024



## Description

The 32Gb Dual Die DDR4 SDRAM uses 16Gb DDR4 SDRAM die; two x8s combined to make one x16. It uses similar signals as the mono x16, and there is one extra ZQ connection for faster ZQ calibration and a BG1 control required for x8 addressing. Refer to Alliance's 16Gb DDR4 SDRAM data sheet (x8 option) for the specifications not included in this document.

#### Features

- Uses two x8 16Gb die to make one x16
- Single-rank DualDie
- $V_{DD} = V_{DDO} = 1.2V (1.14-1.26V)$
- 1.2V V<sub>DDQ</sub>-terminated I/O
- JEDEC-standard ball-out
- Low-profile package

#### Features

- $T_C = 0$ °C to 95°C
  - 0°C to 85°C: 8192 refresh cycles in 64ms
  - 85°C to 95°C: 8192 refresh cycles in 32ms

	2G16
<ul> <li>Configuration <ul> <li>128 Meg x 16 x 16 banks x 1 rank</li> </ul> </li> <li>96-ball FBGA package (Pb-free)</li> </ul>	2010
- 7.5mm x 13mm x 1.2mm  • Timing – cycle time <sup>1</sup>	-62
- 0.625ns @ CL = 22 (DDR4-3200)  • Self refresh  - Standard	None
<ul> <li>Operating temperature         <ul> <li>Commercial (0°C ≤ T<sub>C</sub> ≤ 95°C)</li> </ul> </li> </ul>	None

Table 1: Key Timing Parameters

Speed Grade <sup>1</sup>	Data Rate (MT/s)	Target CL- <b>n</b> RCD- <b>n</b> RP	<sup>t</sup> AA (ns)	<sup>t</sup> RCD (ns)	<sup>t</sup> RP (ns)
-62	3200	22-22-22	13.75	13.75	13.75

Notes: 1. Refer to Speed Bin Tables for additional details.

#### **Table 2: Ordering Information**

Product part No	Org	Temperature Tc	Max Clock (MHz)	Package
AS4C2G16D4-62BCN	2G x 16	Commercial 0°C to 95°C	1600	96-ball FBGA 7.5x13mm

#### Table 3: Addressing

Parameter	2048 Meg x 16
Configuration	128 Meg x 16 x 16 banks x 1 rank
Bank group address	BG[1:0]
Bank count per group	4
Bank address in bank group	BA[1:0]
Row addressing	128K (A[16:0])
Column addressing	1K (A[9:0])
Page size	1KB

Notes: 1. Page size is per bank, calculated as follows:

Page size =  $2^{COLBITS} \times ORG/8$ , where COLBIT = the number of column address bits and ORG = the number of DQ bits.



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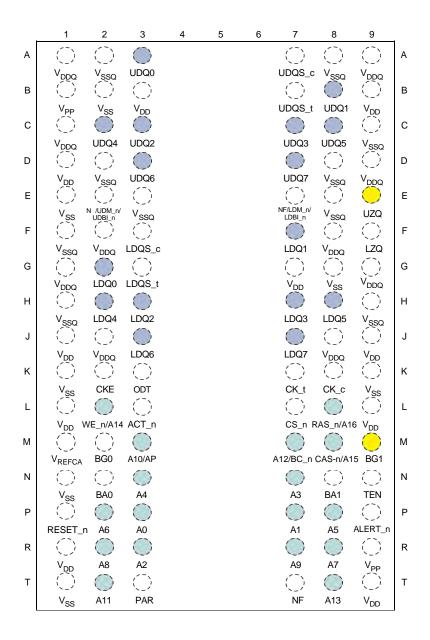
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### Ball Assignments

Figure 1: 96-Ball x16 SR DDP Ball Assignments



Notes: 1. See Ball Descriptions in the monolithic data sheet.

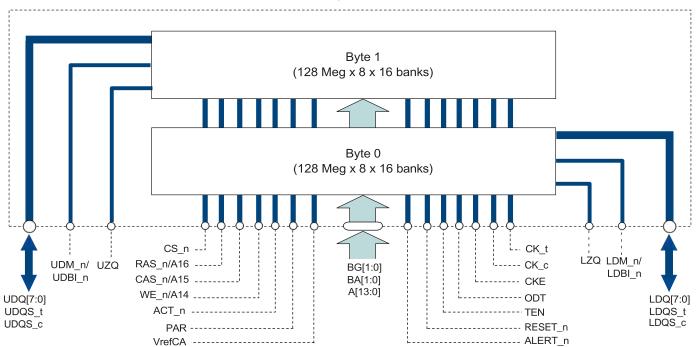
2. A slash "/" defines a mode register selectable function or command/address function. For example: Ball E2 = NF/UDM\_n/UDBI\_n where either NF, UDM\_n, or UDBI\_n is defined via MRS.



### Functional Block Diagrams

Figure 2: Functional Block Diagram (128 Meg x 16 x 16 Banks x 1 Rank)

(128 Meg x 16 x 16 banks)





## Connectivity Test Mode

Connectivity test (CT) mode for the x16 Dual Die single-rank (SR) device is the same as two mono x8 devices connected in parallel. The mapping is restated for clarity.

#### Minimum Terms Definition for Logic Equations

The test input and output pins are related by the following equations, where INV denotes a logical inversion operation and XOR a logical exclusive OR operation:

```
MT0 = XOR (A1, A6, PAR)
MT1 = XOR (A8, ALERT_n, A9)
MT2 = XOR (A2, A5, A13)
MT3 = XOR (A0, A7, A11)
MT4 = XOR (CK_c, ODT, CAS_n/A15)
MT5 = XOR (CKE, RAS_n/A16, A10/AP)
MT6 = XOR (ACT_n, A4, BA1)
MT7L = XOR (BG1, LDM_n/LDBI_n, CK_t)
MT7U = XOR (BG1, UDM_n/UDBI_n, CK_t)
MT8 = XOR (WE_n/A14, A12 / BC, BA0)
MT9 = XOR (BG0, A3, RESET_n and TEN)
```

#### Logic Equations for a x16 **Dual Die**, SR Device

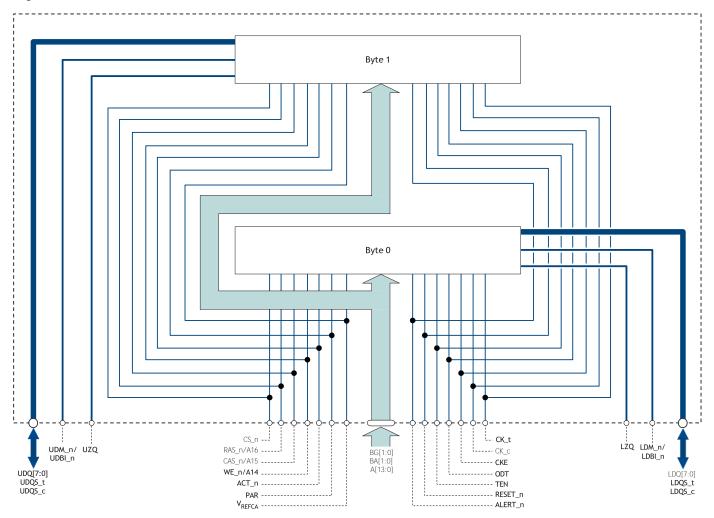
Byte 0	Byte 1
LDQ0 = MT0	UDQ0 = MT0
LDQ1 = MT1	UDQ1 = MT1
LDQ2 = MT2	UDQ2 = MT2
LDQ3 = MT3	UDQ3 = MT3
LDQ4 = MT4	UDQ4 = MT4
LDQ5 = MT5	UDQ5 = MT5
LDQ6 = MT6	UDQ6 = MT6
LDQ7 = MT7L	UDQ7 = MT7U
$LDQS_t = MT8$	$UDQS_t = MT8$
LDQS $c = MT9$	UDQS $c = MT9$

#### x16 **Dual** Die, SR Internal Connections

The figure below shows the internal connections of the x16 Dual Die, SR. The diagram shows why byte 0 and byte 1 outputs have the same logic equations except LDQ7 and UDQ7; they are different because the  $DM_n/DBI_n$  pins are not common for each byte.



Figure 3: x16 Dual Die, SR





### Electrical Specifications - Leakages

Table 4: Input and Output Leakages

Symbol	Parameter	Min	Max	Units	Notes
I <sub>I</sub>	Input leakage current Any input $0V \le V_{IN} \le V_{DD}$ , $V_{REF}$ pin $0V \le V_{IN} \le 1.1V$ (All other pins not under test = $0V$ )		4	μА	1
I <sub>VREF</sub>	V <sub>REF</sub> supply leakage current V <sub>REFDQ</sub> = V <sub>DD</sub> /2 or V <sub>REFCA</sub> = V <sub>DD</sub> /2 (All other pins not under test = 0V)	-4	4	μΑ	2
I <sub>ZQ</sub>	Input leakage on ZQ pin	-50	10	μΑ	
I <sub>TEN</sub>	Input leakage on TEN pin	-12	20	μΑ	
I <sub>OZPD</sub>	Output leakage: V <sub>OUT</sub> = V <sub>DDQ</sub>	-	10	μΑ	3 , 5
I <sub>OZPU</sub>	Output leakage: V <sub>OUT</sub> = V <sub>SSQ</sub>	-50	-	μΑ	3, 4, 5

Notes: 1. Any input 0V < Vin < 1.1V

- 2.  $V_{REFCA} = V_{DD}/2$ ,  $V_{DD}$  at valid level.
- 3. DQs are disabled.
- 4. ODT is disabled with the ODT input HIGH.
- 5. This value needs to be multiplied by 2 for ALERT\_n since it serves both bytes.

### Temperature and Thermal Impedance

It is imperative that the DDR4 SDRAM device's temperature specifications, shown in the following table, be maintained in order to ensure the junction temperature is in the proper operating range to meet data sheet specifications. An important step in maintaining the proper junction temperature is using the device's thermal impedances correctly. The thermal impedances listed in apply to the current die revision and packages.

Incorrectly using thermal impedances can produce significant errors. Read Alliance technical note, "Thermal Applications," prior to using the values listed in the thermal impedance table. For designs that are expected to last several years and require the flexibility to use several DRAM die shrinks, consider using final target theta values (rather than existing values) to account for increased thermal impedances from the die size reduction.

The DDR4 SDRAM device's safe junction temperature range can be maintained when the  $T_C$  specification is not exceeded. In applications where the device's ambient temperature is too high, use of forced air and/or heat sinks may be required to satisfy the case temperature specifications.

Table 5: Thermal Characteristics

Notes 1-3 apply to entire table

Parameter	Symbol	Value	Units	Notes
Operating temperature	T <sub>C</sub>	0 to 85	°C	
		0 to 95	°C	4

Notes: 1. MAX operating case temperature  $T_{\mathbb{C}}$  is measured in the center of the package, as shown below.

- 2. A thermal solution must be designed to ensure that the device does not exceed the maximum  $T_C$  during operation.
- 3. Device functionality is not guaranteed if the device exceeds maximum  $T_{\mathbb{C}}$  during operation.
- 4. If  $T_C$  exceeds 85°C, the DRAM must be refreshed externally at 2x refresh, which is a 3.9 $\mu$ s interval refresh rate. The use of self refresh temperature (SRT) or automatic self refresh (ASR), if available, must be enabled.

Figure 4: Temperature Test Point Location

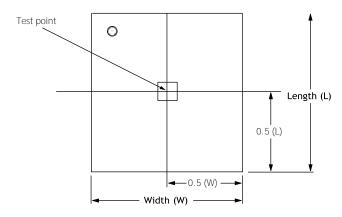


Table 6: Thermal Impedance

Package	Substrate	O JA (°C/W) Airflow = Om/s	• JA (°C/W) Airflow = 1m/s	O JA (°C/W) Airflow = 2m/s	<b>O</b> JB (°C/W)	O JC (°C/W)	Notes
96-ball	Low conductivity	48.7	36.9	32.4	NA	2.6	1
	High conductivity	28.7	23.7	22.0	9.7	NA	

Notes: 1. Thermal resistance data is based on a typical number.

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## DRAM Package Electrical Specifications

Table 7: DRAM Package Electrical Specifications for x16 DDP Devices

Notes 1-2 apply to the entire table

				1866, 2133, 2933, 3200		
Parameter		Symbol	Min	Max	Unit	Notes
Input/output	Zpkg	Z <sub>IO</sub>	35	60	ohm	3
	Package delay	Td <sub>IO</sub>	60	120	ps	3
	Lpkg	L <sub>IO</sub>	-	5.5	nH	
	Cpkg	C <sub>IO</sub>	-	4	pF	
DQSL_t/DQSL_c/D QSU_t/DQSU_c	Zpkg	Z <sub>IO DQS</sub>	35	60	ohm	
	Package delay	Td <sub>IO DQS</sub>	60	120	ps	
	Lpkg	L <sub>IO DQS</sub>	-	5.5	nH	
	Cpkg	C <sub>IO DQS</sub>	-	4	pF	
DQSL_t/DQSL_c,	Delta Zpkg	DZ <sub>IO DQS</sub>	-	5	ohm	4
DQSU_t/DQSU_c,	Delta delay	DTd <sub>IO DQS</sub>	-	5	ps	4
Input CTRL pins	Zpkg	Z <sub>I CTRL</sub>	30	70	ohm	5
	Package delay	Td <sub>I CTRL</sub>	60	120	ps	5
	Lpkg	L <sub>I CTRL</sub>	-	7.5	nH	
	Cpkg	C <sub>I CTRL</sub>	-	4	рF	
Input CMD ADD	Zpkg	Z <sub>I ADD CMD</sub>	30	60	ohm	6
pins	Package delay	Td <sub>I ADD CMD</sub>	60	120	ps	6
	Lpkg	L <sub>I ADD CMD</sub>	-	7.5	nH	
	Cpkg	C <sub>I ADD CMD</sub>	-	4	pF	
CK_t, CK_c	Zpkg	Z <sub>CK</sub>	30	60	ohm	
	Package delay	Td <sub>CK</sub>	60	120	ps	
	Delta Zpkg	DZ <sub>DCK</sub>	-	5	ohm	7
	Delta delay	DTd <sub>DCK</sub>	-	5	ps	7
Input CLK	Lpkg	L <sub>I CLK</sub>	-	7.5	nH	
	Cpkg	C <sub>I CLK</sub>	-	4	рF	
ZQ Zpkg		Z <sub>O ZQ</sub>	-	50	ohm	
ZQ delay		Td <sub>O ZQ</sub>	30	135	ps	
ALERT Zpkg		Z <sub>O ALERT</sub>	30	60	ohm	
ALERT delay		Td <sub>O ALERT</sub>	60	110	ps	
			1	1	1	

Notes: 1. The values in this table are guaranteed by design/simulation only, and are not subject to production testing.



- 2. Package implementations should satisfy targets if the Zpkg and package delay fall within the ranges shown, and the maximum Lpkg and Cpkg do not exceed the maximum values shown. The package design targets are provided for reference, system signal simulations should not use these values but use the Alliance package model.
- 3.  $Z_{IO}$  and  $Td_{IO}$  apply to DQ, DM, DQS\_c, DQS\_t, TDQS\_t, and TDQS\_c.
- 4. Absolute value of ZIO (DQS\_t), ZIO (DQS\_c) for impedance (Z) or absolute value of TdIO (DQS\_t), TdIO (DQS\_c) for delay (Td).
- 5.  $Z_{ICTRL}$  and  $Td_{ICTRL}$  apply to ODT, CS\_n, and CKE.
- 6.  $Z_{IADD\ CMD}$  and  $Td_{IADD\ CMD}$  apply to A[17:0], BA[1:0], BG[1:0], RAS\_n CAS\_n, and WE\_n.
- 7. Absolute value of ZCK\_t, ZCK\_c for impedance (Z) or absolute value of TdCK\_t, TdCK\_c for delay (Td).

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### Current Specifications - Limits

Table 8: DDR4 x16 **Dual** Die  $I_{CDD}$  and  $I_{CPP}$  Specifications and Conditions - (0 ≤  $T_{C}$  ≤ 85°C)

Notes 1 and 2 apply to the entire table

Combined Symbol	Individual Die Status	DDR4-2133	DDR4-2400	DDR4-2666	DDR4-2933	DDR4-3200	Units
I <sub>CDD0</sub>	I <sub>CDD0</sub> = I <sub>DD0</sub> * 2	132	134	136	138	140	mA
I <sub>CPP0</sub>	I <sub>CPP0</sub> = I <sub>PP0</sub> * 2	8	8	8	8	8	mA
I <sub>CDD1</sub>	I <sub>CDD1</sub> = I <sub>DD1</sub> * 2	160	162	164	166	168	mA
I <sub>CDD2N</sub>	$I_{CDD2N} = I_{DD2N} * 2$	82	84	86	88	90	mA
I <sub>CDD2NT</sub>	$I_{CDD2NT} = I_{DD2NT} * 2$	108	110	112	114	116	mA
I <sub>CDD2P</sub>	$I_{CDD2P} = I_{DD2P} * 2$	76	76	76	76	76	mA
I <sub>CDD2Q</sub>	$I_{CDD2Q} = I_{DD2Q} * 2$	84	84	84	84	84	mA
I <sub>CDD3N</sub>	$I_{CDD3N} = I_{DD3N} * 2$	116	118	120	122	124	mA
I <sub>CPP3N</sub>	I <sub>CPP3N</sub> = I <sub>PP3N</sub> * 2	4	4	4	4	4	mA
I <sub>CDD3P</sub>	$I_{CDD3P} = I_{DD3P} * 2$	94	96	98	100	102	mA
I <sub>CDD4R</sub>	$I_{CDD4R} = I_{DD4R} * 2$	282	308	334	360	386	mA
I <sub>CDD4W</sub>	$I_{CDD4W} = I_{DD4W} * 2$	202	222	242	262	282	mA
I <sub>CDD5R</sub>	$I_{CDD5R} = I_{DD5R} * 2$	136	136	136	136	136	mA
I <sub>CPP5R</sub>	I <sub>CPP5R</sub> = I <sub>PP5R</sub> * 2	8	8	8	8	8	mA
I <sub>CDD6N</sub>	$I_{CDD6N} = I_{DD6N} * 2$	106	106	106	106	106	mA
I <sub>CDD6</sub> <sup>3</sup>	I <sub>CDD6E</sub> = I <sub>DD6E</sub> * 2	180	180	180	180	180	mA
I <sub>CDD6R</sub> 3	$I_{CDD6R} = I_{DD6R} * 2$	40	40	40	40	40	mA
I <sub>CDD6A</sub> (25°C) <sup>3</sup>	I <sub>CDD6A</sub> = I <sub>DD6A</sub> * 2	22	22	22	22	22	mA
I <sub>CDD6A</sub> (45°C) <sup>3</sup>	I <sub>CDD6A</sub> = I <sub>DD6A</sub> * 2	40	40	40	40	40	mA
I <sub>CDD6A</sub> (75°C) <sup>3</sup>	$I_{CDD6A} = I_{DD6A} * 2$	102	102	102	102	102	mA
I <sub>CDD6A</sub> (95°C) <sup>3</sup>	$I_{CDD6A} = I_{DD6A} * 2$	180	180	180	180	180	mA
I <sub>CPP6x</sub> <sup>3</sup>	I <sub>CPP6x</sub> = I <sub>CPP6x</sub> * 2	12	12	12	12	12	mA
I <sub>CDD7</sub>	I <sub>CDD7</sub> = I <sub>DD7</sub> * 2	400	400	400	400	400	mA
I <sub>CPP7</sub>	I <sub>CPP7</sub> = I <sub>PP7</sub> * 2	26	26	26	26	26	mA
I <sub>CDD8</sub>	I <sub>CDD8</sub> = I <sub>DD8</sub> * 2	72	72	72	72	72	mA

Notes: 1. I<sub>CDD</sub> values reflect the combined current of both individual die. I<sub>DDX</sub> represents individual die values.

<sup>2.</sup>  $I_{CDD}$  values must be derated (increased) when operated outside of the range 0°C  $\leq$   $T_{C} \leq$  85°C. They must also be derated when using features such as CAL, CA parity, read/write DBI, AL, gear-down, write CRC, 2X/4X REF, and DLL disabled. Refer to the 16Gb monolithic data sheet for all derating values. Derating values apply to each individual  $I_{DDX}$  that make up the combined  $I_{CDD}$ .



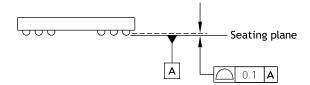
3. I<sub>CDD6R</sub>, I<sub>CDD6A</sub>, and I<sub>CDD6E</sub> values are verified by design and characterization, and may not be subject to production test.

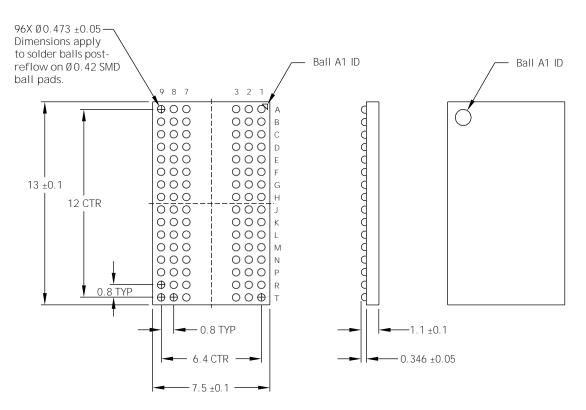
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### Package Dimensions

Figure 5: 96-Ball FBGA





Notes: 1. All dimensions are in millimeters.

2. Solder ball material: SACQ (92.5% Sn, 4% Ag, 3% Bi, 0.5% Cu).

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#### PART NUMBERING SYSTEM

AS4C	<b>2</b> G16D4	-62	В	С	N	XX
DRAM	<b>2</b> G16= <b>2</b> G x 16 D4=DDR4	62=1600 MHz	B=FBGA	C=Commercial temp 0°C~ 95°C	Indicates Pb and Halogen Free	Packing Type None:Tray TR:Reel



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